JEDEC STANDARD

Low Temperature Storage Life

JESD22-A119A

(Revision of JESD22-A119, November 2004, Reaffirmed September 2009)

OCTOBER 2015

JEDEC SOLID STATE TECHNOLOGY ASSOCIATION



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TEST METHOD A119A

TEMPERATURE STORAGE LIFE

(From JEDEC Board Ballot JCB-15-50, formulated under the cognizance of JC-14.1 Subcommittee on Reliability Test Methods for Packaged Devices.)

1	Scope			
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The test is applicable for evaluation, screening, monitoring, and/or qualification of all solid state devices.

Low Temperature storage test is typically used to determine the effect of time and temperature, under storage conditions, for thermally activated failure mechanisms of solid state electronic devices, including nonvolatile memory devices (data retention failure mechanisms). During the test reduced temperatures (test conditions) are used without electrical stress applied. This test may be destructive, depending on Time, Temperature and Packaging (if any).

2 Apparatus

2.1 Low temperature storage chambers

The apparatus required for this test shall consist of a controlled temperature chamber capable of maintaining the specified temperature over the entire sample population under test.

2.2 Electrical test equipment

Electrical equipment capable of performing the appropriate measurements for the devices being tested, including write and verify the required data retention pattern(s) for nonvolatile memories.

Test Method A119A (Revision of A119)

3 Procedure

3.1 Low temperature storage conditions

The Devices under test shall be subjected to continuous storage at one of the Temperature Conditions of Table 1.

Table 1 — Low Temperature storage conditions
Condition A: -40 (-10/+0) °C
Condition B: -55 (-10/+0) °C
Condition C: -65 (-10/+0) °C

NOTE CAUTION should be exercised when selecting an accelerated test condition since the accelerated temperature used may exceed the capabilities of the device and materials, thereby inducing overstress failures that would not occur under normal use conditions.

The devices may be returned to room ambient conditions for interim electrical measurements.

3.2 **Measurements**

Unless otherwise specified, interim and final electrical test measurements shall be completed within 96 hours after removal of the devices from the specified test conditions. Intermediate measurements are optional unless otherwise specified.

The electrical test measurements shall consist of parametric and functional tests specified in the applicable procurement document. For nonvolatile memories, the data specified data retention pattern must be written initially, and then subsequently verified without re-writing.

3.3 **Failure criteria**

A device will be considered a Low Temperature Storage failure if parametric limits are exceeded, or if functionality cannot be demonstrated under nominal and worst-case conditions, as specified in the applicable procurement document. For nonvolatile memories, the specified data retention pattern shall be verified before and after storage. A margin test may be used to detect data retention degradation.

Mechanical damage, such as cracking, chipping, or breaking of the package, (as defined in JESD22-B101) will be considered a failure, provided that such damage was not induced by fixtures or handling and it is critical to the package performance in the specific application.

Cosmetic package defects and degradation of lead finish, or solderability are not considered valid failure criteria for this stress.

Test Method A119A (Revision of A119)

4 Summary

The following details shall be specified in the applicable procurement document.

- a) Electrical test measurements
- b) Sample size and number of failures (specify zero if none observed)
- c) Condition per Table 1, and duration of stress
- d) Intermediate electrical test measurements, if required
- e) Nonvolatile memory data retention pattern (for appropriate devices)

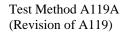
Annex A (informative) Differences between JESD22-A119A and JESD22-A119

This annex briefly describes most of the changes made to entries that appear in this standard, JESD22-A119A, compared to its predecessor, JESD22-A119 (November 2004). If the change to a concept involves any words added or deleted (excluding deletion of accidentally repeated words), it is included. Some punctuation changes are not included.

Description of change Clause

4

Item C was modified to remove the recommended duration of 168 hours. There are no known published reliability models that supported this duration.





Standards Improvement Form	JE	DEC	JESD22-A119A				
The purpose of this form is to provide the Technical Committees of JEDEC with input from the industry regarding usage of the subject standard. Individuals or companies are invited to submit comments to JEDEC. All comments will be collected and dispersed to the appropriate committee(s).							
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I recommend changes to the following: Requirement, clause number							
Test method number	Clause number		7				
The referenced clause number has proven to be:	C ^O X	- Bla					
Other							
2. Recommendations for correction:	ARXS						
	λ						
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